

Abstract

Method for depositing an epitaxial layer on a substrate wafer of semiconductor material in a deposition apparatus

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A method for depositing an epitaxial layer on a substrate wafer of semiconductor material in a deposition apparatus, comprising

the placing of the substrate wafer on a susceptor of the deposition apparatus, which is surrounded, separated by a gap, from a preheat ring and is held by a supporting shaft;

10 the determining of an excentricity between an axis perpendicularly through the center of the preheat ring and an axis perpendicularly through the center of the susceptor;

the passing of deposition gas over the substrate wafer along a flow direction pointing from a gas inlet to a gas outlet;

15 the passing of purge gas along a lower side of a preheat ring and a lower side of the susceptor;

the rotating of the supporting shaft about an axis of rotation with a frequency;

which comprises

the displacing of the supporting shaft from a starting position in which its axis of rotation is arranged along the axis perpendicularly through the center of the preheat

20 ring to an end position and back to the starting position with the frequency of the rotating of the supporting shaft, the displacement path from the starting position to the end position being dependent on the excentricity.

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Drawing for the Abstract: Fig. 3